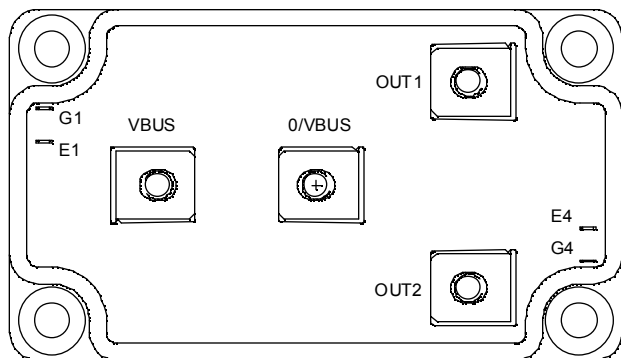
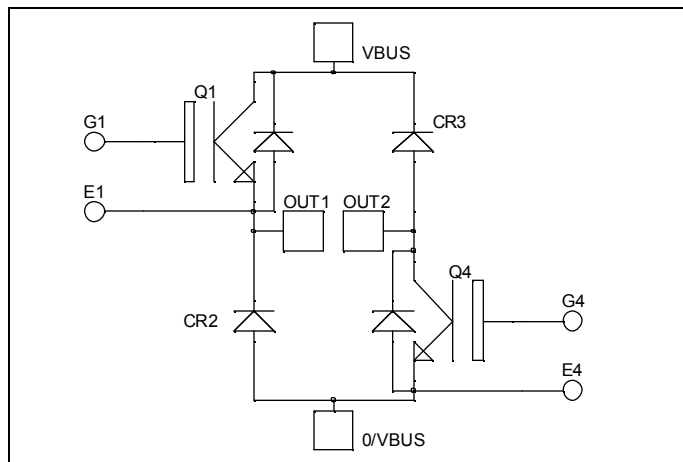


Asymmetrical - Bridge Trench + Field Stop IGBT® Power Module

$V_{CES} = 1700V$
 $I_C = 100A @ T_c = 80^\circ C$



Application

- Welding converters
- Switched Mode Power Supplies
- Switched Reluctance Motor Drives

Features

- Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1700	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$ $T_C = 80^\circ C$	A
		150 100	
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	200
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$	560
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	200A @ 1600V



CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}$, $V_{CE} = 1700\text{V}$			350	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 100\text{A}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	2.0 2.4	2.4	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 2\text{mA}$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}$, $V_{CE} = 0\text{V}$			500	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}$		9		nF
C_{oes}	Output Capacitance	$V_{CE} = 25\text{V}$		0.36		
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		0.3		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		370		ns
T_r	Rise Time	$V_{GE} = 15\text{V}$ $V_{Bus} = 900\text{V}$		40		
$T_{d(off)}$	Turn-off Delay Time	$I_C = 100\text{A}$		650		
T_f	Fall Time	$R_G = 4.7\ \Omega$		180		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C)		400		ns
T_r	Rise Time	$V_{GE} = 15\text{V}$ $V_{Bus} = 900\text{V}$		50		
$T_{d(off)}$	Turn-off Delay Time	$I_C = 100\text{A}$		800		
T_f	Fall Time	$R_G = 4.7\ \Omega$		300		
E_{on}	Turn-on Switching Energy			32		mJ
E_{off}	Turn-off Switching Energy			31		

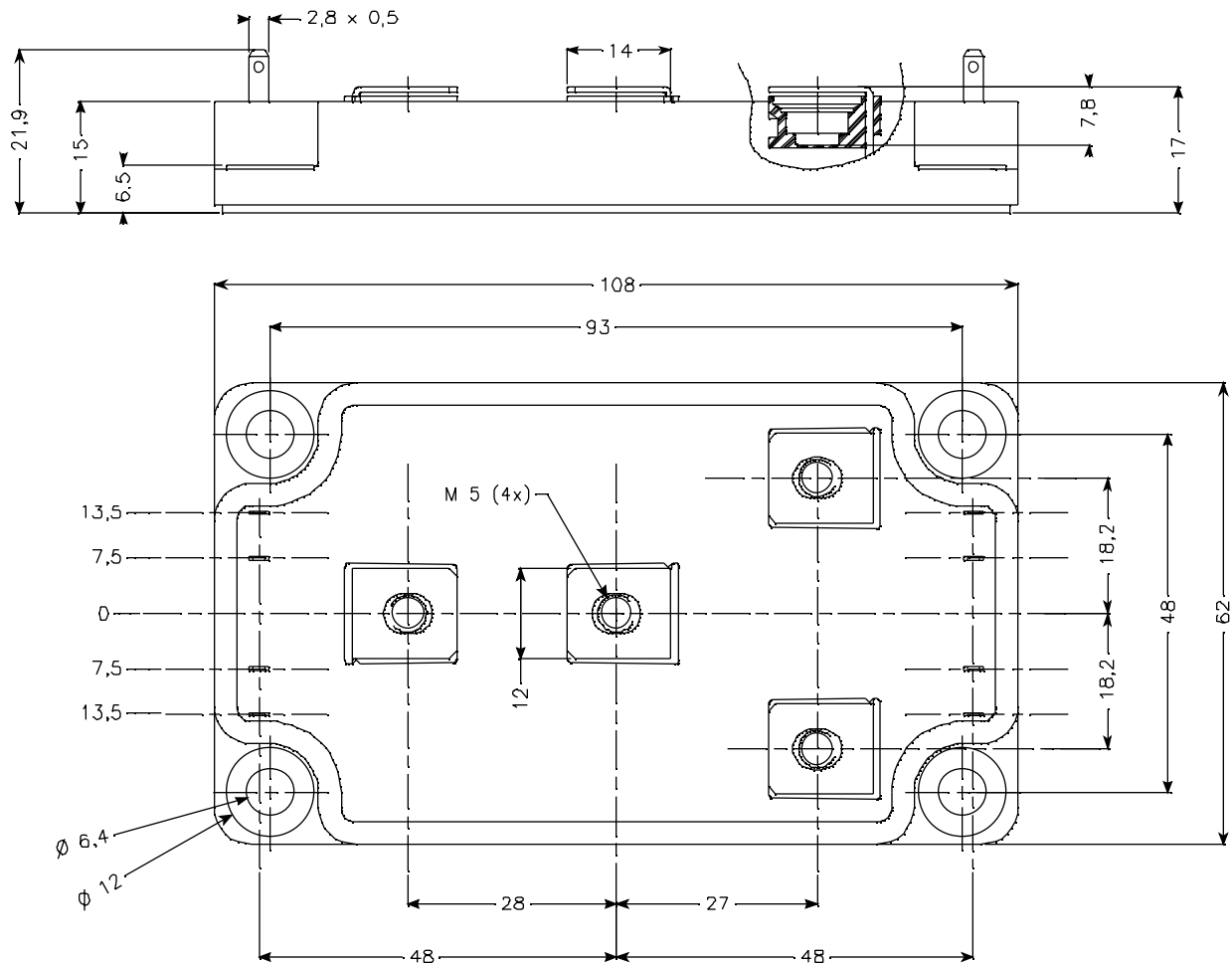
Diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1700			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1700\text{V}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		350 600	μA
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle	$T_c = 80^\circ\text{C}$	100		A
V_F	Diode Forward Voltage	$I_F = 100\text{A}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	1.8 1.9	2.2	V
t_{rr}	Reverse Recovery Time	$I_F = 100\text{A}$ $V_R = 900\text{V}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	385 490		ns
Q_{rr}	Reverse Recovery Charge	$di/dt = 1600\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	28 46		μC

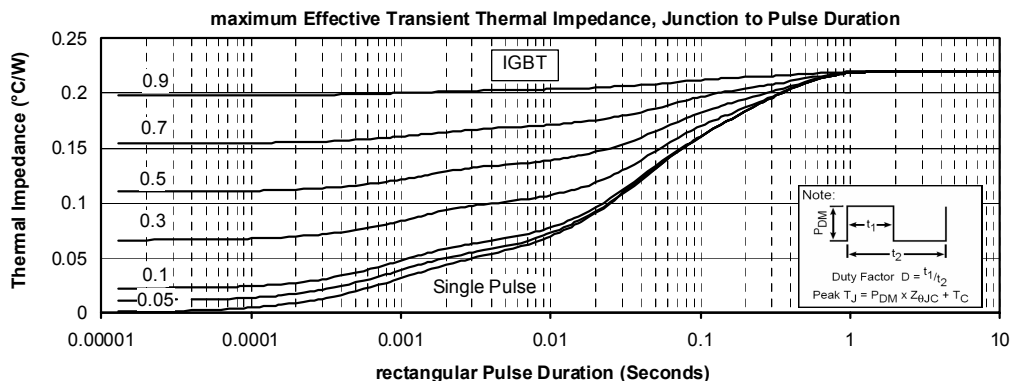
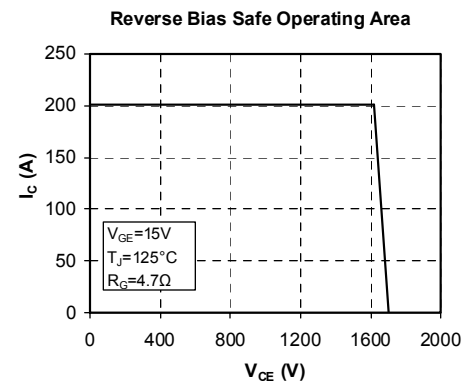
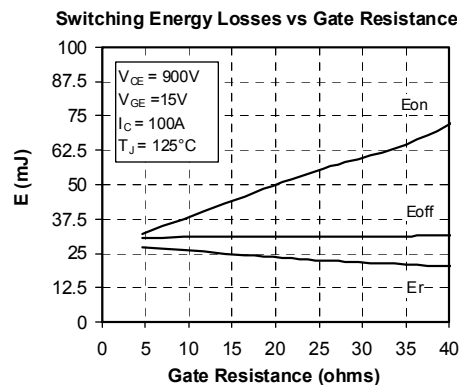
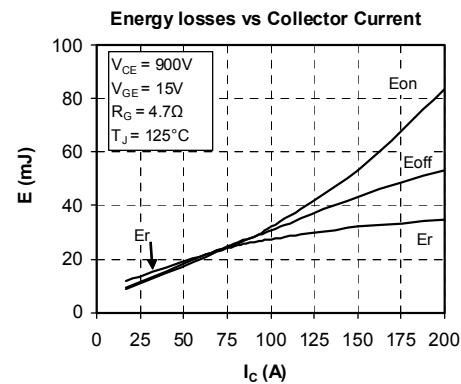
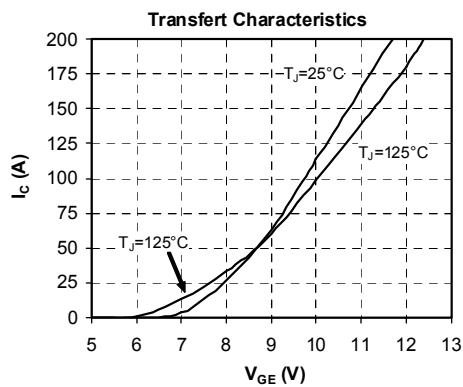
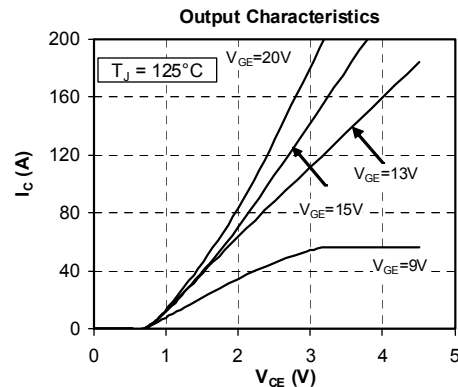
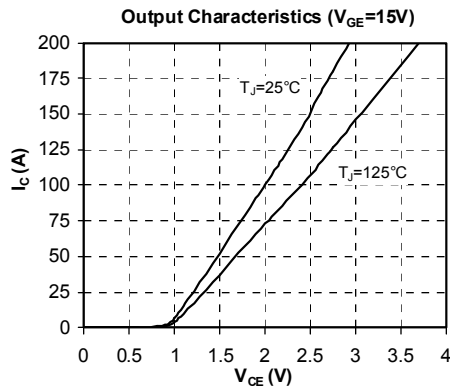
Thermal and package characteristics

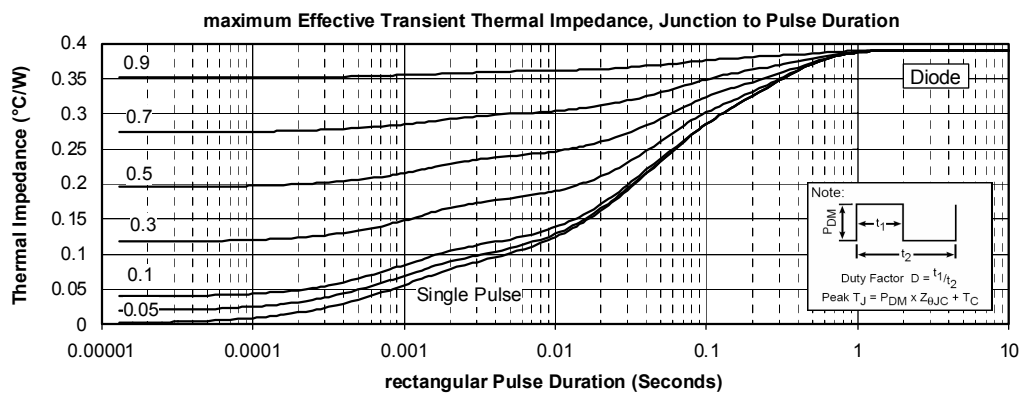
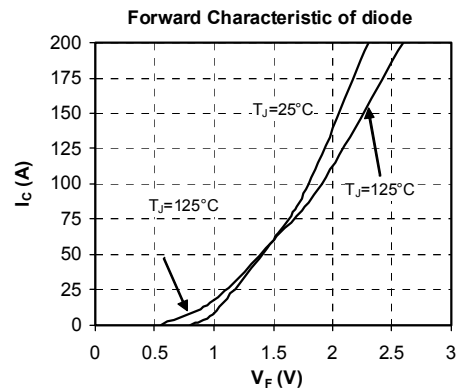
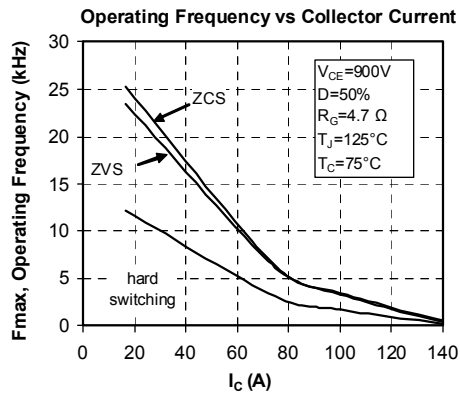
Symbol	Characteristic			Min	Typ	Max	Unit
R _{thJC}	Junction to Case			IGBT		0.22	°C/W
				Diode		0.39	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I isol<1mA, 50/60Hz			3400			V
T _J	Operating junction temperature range			-40		150	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	
Wt	Package Weight					280	g

Package outline (dimensions in mm)



Typical Performance Curve





APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.